

L9	792	438/398.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:06
L10	1	9 and trench adj capacitor and (substrate with etch\$4) and metal adj silicide and lower adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:06
L11	10	8 and trench adj capacitor and (substrate with etch\$4) and metal adj silicide and lower adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:06
L12	3	7 and trench adj capacitor and (substrate with etch\$4) and metal adj silicide and lower adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:07
L13	8	4 and trench adj capacitor and (substrate with etch\$4) and metal adj silicide and lower adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:07
L14	4	3 and trench adj capacitor and (substrate with etch\$4) and metal adj silicide and lower adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:07

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	35	trench adj capacitor and (substrate with etch\$4) and metal adj silicide and lower adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:01
L2	35	trench adj capacitor and (substrate with etch\$4) and metal adj silicide and lower adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:06
L3	773	438/243.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:05
L4	2425	438/253.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:05
L5	748	438/296.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:05
L6	587	438/286.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:05
L7	673	438/386.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:06
L8	4400	438/396.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/19 13:06